

## Electronic Supporting Information (ESI)

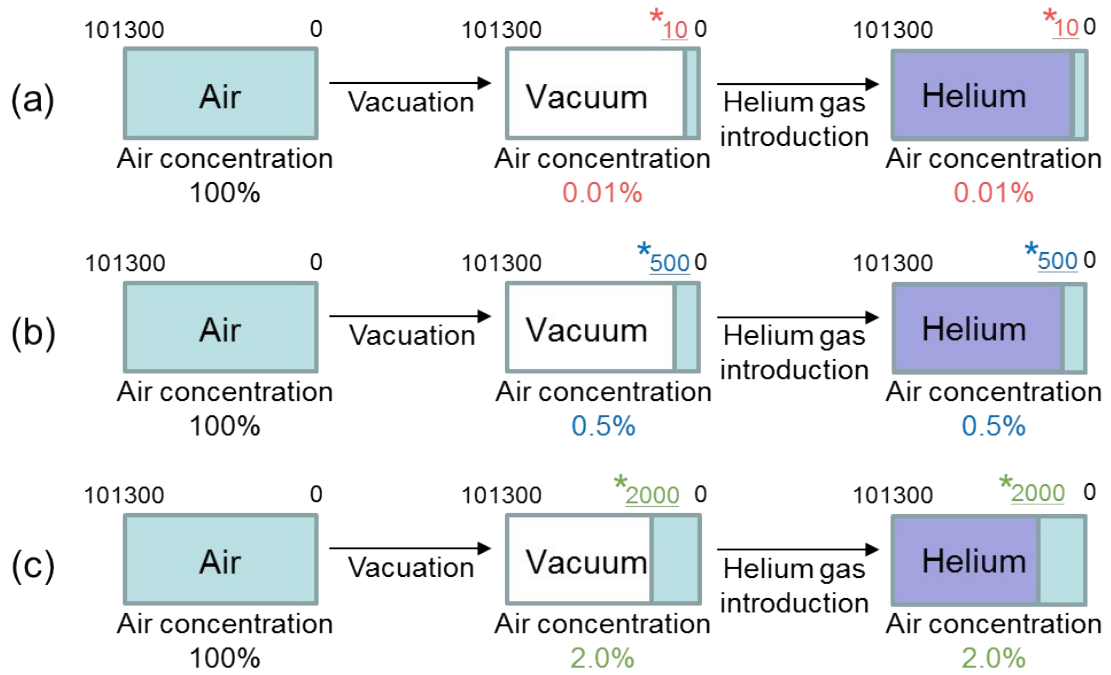
### **Influence of air contamination during heat-assisted plasma treatment on adhesion property of polytetrafluoroethylene (PTFE)**

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**ESI-1** Schematic of the relation between the backpressure in the chamber and the air concentration: (a) backpressure of 10 Pa and air concentration of 0.01%, (b) backpressure of 500 Pa and air concentration of 0.5%, and (c) backpressure of 2000 Pa and air concentration of 2.0%. The \* symbol and underlining denote the backpressure.

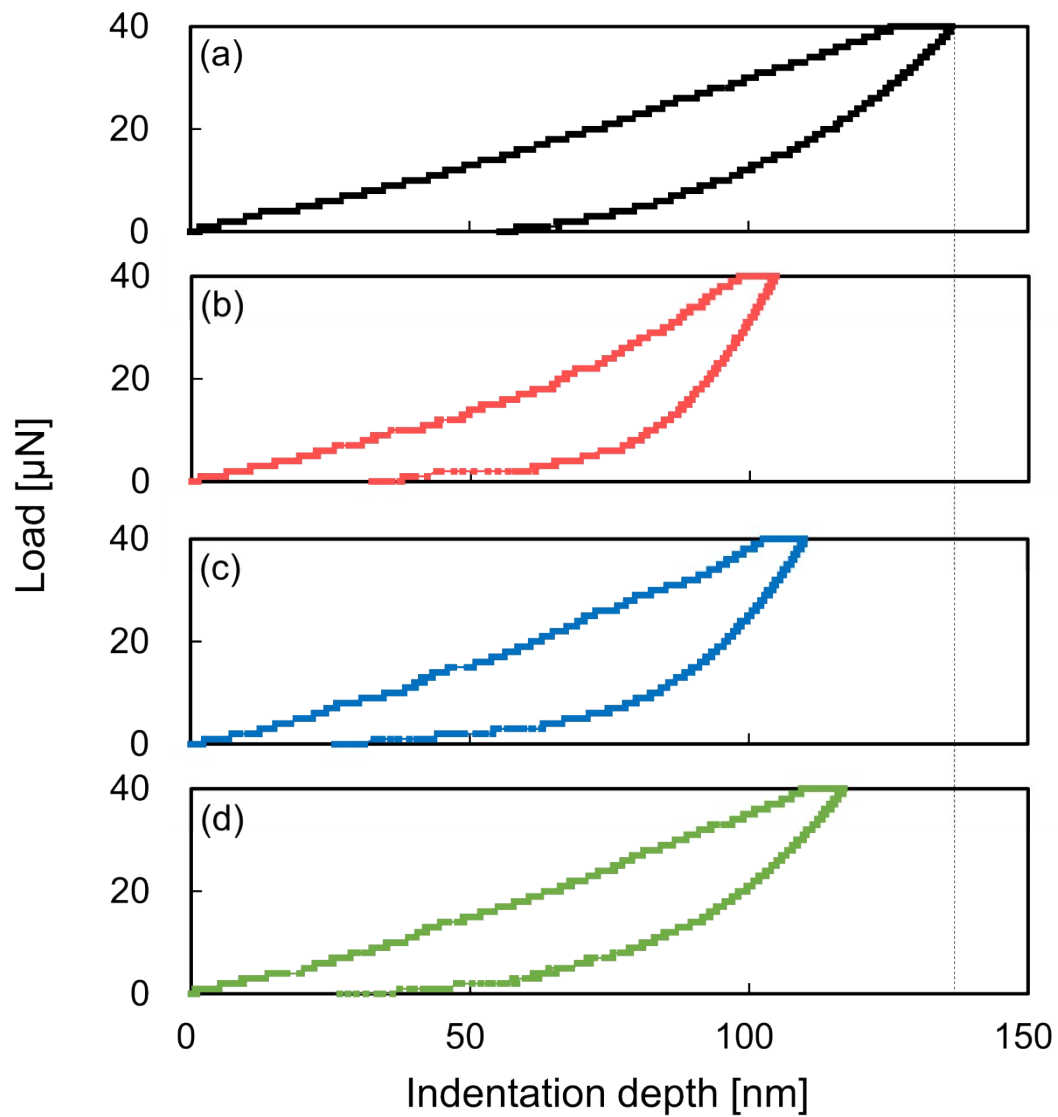
**ESI-2** Gas compositions of the different air concentrations used for HAP treatment. The data were derived from the OES spectra (**Fig. 1**), and each peak intensity was normalized to the peak intensity of helium at 706 nm.

<b>Species</b>	<b>Wavelength [nm]</b>	<b>0.01% air</b>	<b>0.5% air</b>	<b>2.0% air</b>
OH	309	5	13	19
N <sub>2</sub>	337	1	125	172
He	706	100	100	100
O	777	14	21	26

**ESI-3** PTFE sample weight before and after treatment and average etching depth with or without HAP treatments in different air concentrations.

<b>Treatment</b>	<b>Trial</b>	<b>Weight before treatment [mg]</b>	<b>Weight after treatment [mg]</b>	<b>Change in weight [mg]</b>	<b>Average change in weight [mg]</b>	<b>Average change in depth <sup>a)</sup> [<math>\mu</math>m]</b>
Heating only	1	1302.6	1302.2	0.4		
	2	1345.6	1345.3	0.3	0.2	0.0
	3	1365.5	1365.5	0.0		
0.01% air	1	1357.5	1349.4	8.1		
	2	1351.9	1344.8	7.1	8.5	0.4
	3	1377.5	1367.3	10.2		
0.5% air	1	1353.4	1325.9	27.5		
	2	1355.0	1333.0	22.0	23.7	1.1
	3	1379.2	1357.5	21.7		
2.0% air	1	1364.2	1329.6	34.6		
	2	1355.4	1317.0	38.4	35.2	1.6
	3	1333.4	1300.7	32.7		

<sup>a)</sup> The average etching depth was calculated under the assumption that the specific weight of PTFE is 2.150 g·cm<sup>-3</sup>.



**ESI-4** Representative load-depth curves of PTFE samples without or with HAP treatments in different air concentrations: (a) as-received, (b) HAP-treated in 0.01% air, (c) HAP-treated in 0.5% air, and (d) HAP-treated in 2.0% air.